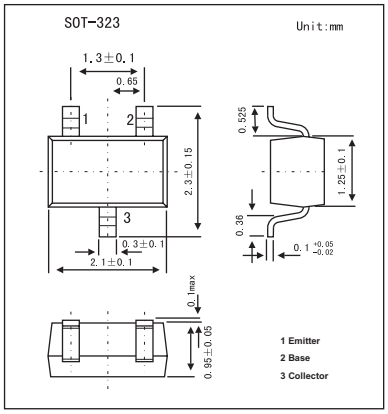
Silicon PNP Epitaxial Planar Type

2SB1218



■ Features

● High forward current transfer ratio h_{FE}.

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	-45	V
Collector-emitter voltage	V_{CEO}	-45	V
Emitter-base voltage	V_{EBO}	-7	V
Peak collector current	I_{CP}	-200	A
Collector current	I_C	-100	A
Collector power dissipation	P_C	150	mW
Junction temperature	T_j	150	℃
Storage temperature	T_{stg}	-55 to +150	℃

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-base voltage	V_{CBO}	I_C = -10 μA, I_E = 0	-45			V
Collector-emitter voltage	V_{CEO}	I_C = -2 mA, I_B = 0	-45			V
Emitter-base voltage	V_{EBO}	I_E = -10 μA, I_C = 0	-7			V
Collector-base cutoff current	I_{CBO}	V_{CB} = -20 V, I_E = 0			-0.1	μA
Collector-emitter cutoff current	I_{CEO}	V_{CE} = -10 V, I_B = 0			-100	μA
Forward current transfer ratio	h_{FE}	V_{CE} = -10 V, I_C = -2 mA	160		460	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C = -100 mA, I_B = -10 mA		-0.3	-0.5	V
Transition frequency	f_T	V_{CB} = -10 V, I_E = 1 mA, f = 200 MHz		80		MHz
Collector output capacitance	C_{ob}	V_{CB} = -10 V, I_E = 0, f = 1 MHz		2.7		pF

■ h_{FE} Classification

Marking	BQ	BR	BS	B
Rank	Q	R	S	No-rank
h_{FE}	160～260	210～340	290～460	160～460